

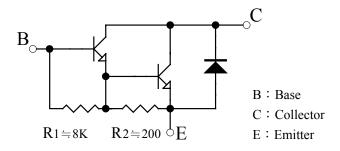
# NPN EPITAXIAL PLANAR TRANSISTOR

#### **■** DESCRIPTION

The **2SD2195** is designed for use in general purpose amplifier and low speed switching application.



#### ■ Equivalent Circuit



#### ■ ABSOLUTE MAXIMUM RATING (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		$V_{CBO}$	150	V
Collector-Emitter Voltage		$V_{CEO}$	100	V
Emitter-Base Voltage		$V_{EBO}$	4	V
Collector Current	DC	lc	2	^
	Pulse(Note 2)		4	А
Collector Dissipation		Pc	0.6	W
Junction Temperature		TJ	+125	°C
Storage Temperature		$T_{STG}$	-55 ~ <b>+</b> 150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse test: Pulse Width  $\leq$  350 $\mu$ s, Duty Cycle  $\leq$  2%.

## ■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient	SOT-89	$\theta_{JA}$	208	°C/W	

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.



### **■ ELECTRICAL CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =100μA, I <sub>E</sub> =0	150			V			
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	$I_{C}=20\mu A, I_{B}=0$	100			V			
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	$V_{CE}$ =4V, $I_{C}$ =2A			2.8	V			
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =100V, I <sub>E</sub> =0			1	mA			
Collector Cutoff Current	I <sub>CEO</sub>	V <sub>CE</sub> =50V, I <sub>B</sub> =0			2	mA			
Emitter Cutoff Current	I <sub>EBO</sub>	$V_{EB}$ =5 $V$ , $I_{C}$ =0			2.5	mA			
ON CHARACTERISTICS									
DC Current Gain (Note)	h <sub>FE</sub>	V <sub>CE</sub> =4V, I <sub>C</sub> =1A	1000						
		V <sub>CE</sub> =4V, I <sub>C</sub> =2A	500						
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =2A, I <sub>B</sub> =2mA			2	V			
SMALL-SIGNAL CHARACTERISTICS									
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0A, f=1MHz			200	pF			

Note: Pulse test: Pulse Width ≦ 380μs, Duty Cycle ≦ 2%

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